

L & S BAND GaAs FET [SMD non – matched]**DESCRIPTION**

The MGF0921A GaAs FET with an N-channel schottky Gate, is designed for use UHF band amplifiers.

FEATURES

- High output power
Po=33dBm(TYP.) @f=1.9GHz,Pin=17dBm
- High power gain
Gp=17dB(TYP.) @f=1.9GHz
- High power added efficiency
 η_{add} =40%(TYP.) @f=1.9GHz,Pin=17dBm
- Hermetic Package

APPLICATION

- For UHF Band power amplifiers

QUALITY

- GG

RECOMMENDED BIAS CONDITIONS

- Vds=10V • Ids=500mA • Rg=200 Ω

Delivery -01:Tape & Reel(1K), -03:Trai(50pcs)

Absolute maximum ratings (Ta=25°C)

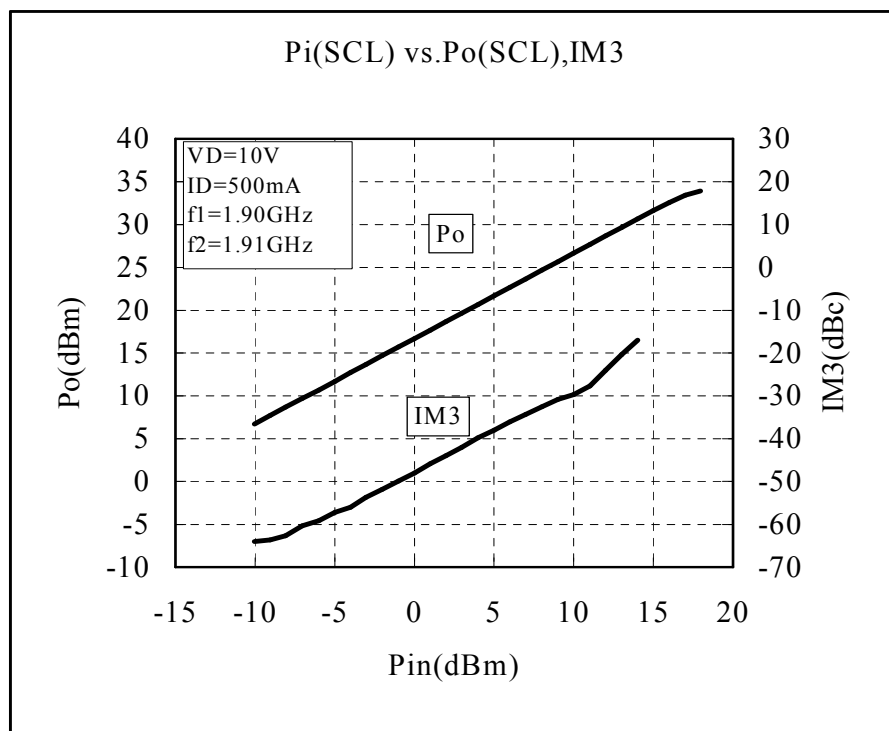
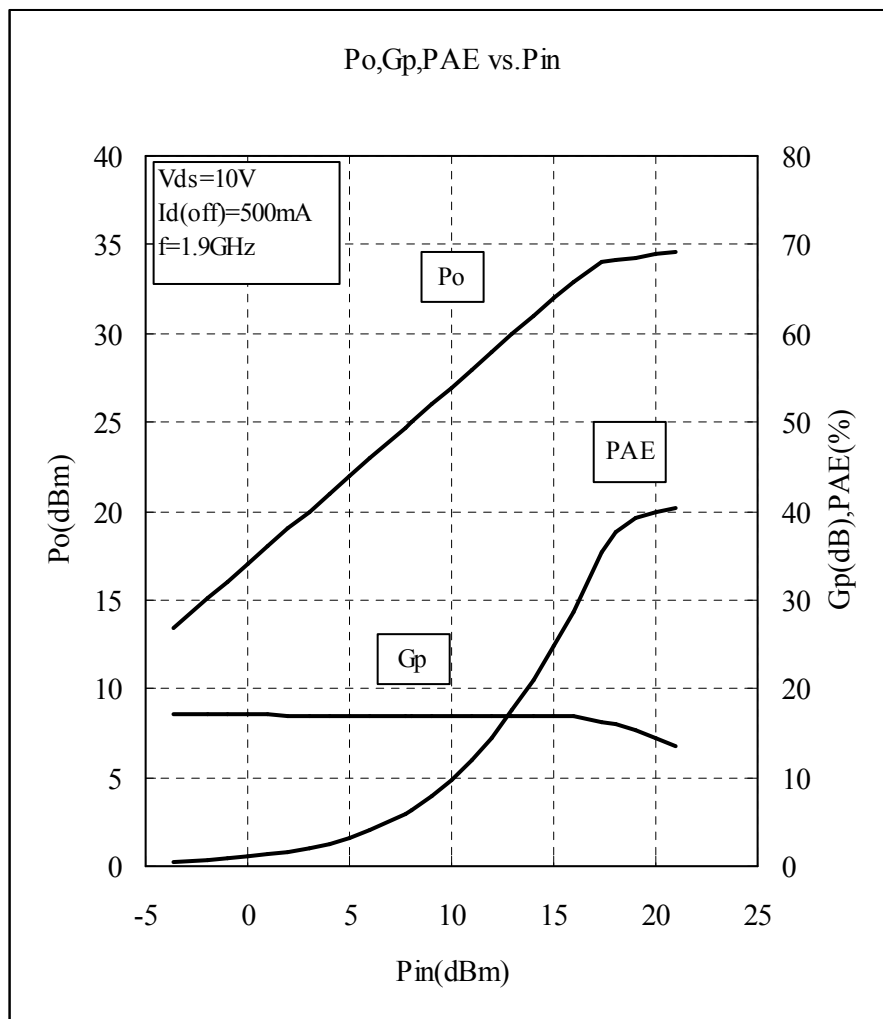
Symbol	Parameter	Ratings	Unit
VGSO	Gate to sourcebreakdown voltage	-15	V
VGDO	Gate to drain breakdown voltage	-15	V
ID	Drain current	1800	mA
IGR	Reverse gate current	-5.0	mA
IGF	Forward gate current	15	mA
PT	Total power dissipation	10	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

Fig.1**Electrical characteristics** (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	--	1100	1800	mA
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=4.0mA	-1.0	-	-5.0	V
gm	Transconductance	VDS=3V,ID=500mA	-	370	-	mS
Po	Output power	VDS=10V,ID=500mA,f=1.9GHz Pin=17dBm	31	33	-	dBm
η_{add}	Power added Efficiency		-	38	-	%
GLP	Linear Power Gain	VDS=10V,ID=500mA,f=1.9GHz	15	17	-	dB
Rth(ch-c)	Thermal Resistance *1	ΔV_f Method	-	11	15	°C/W

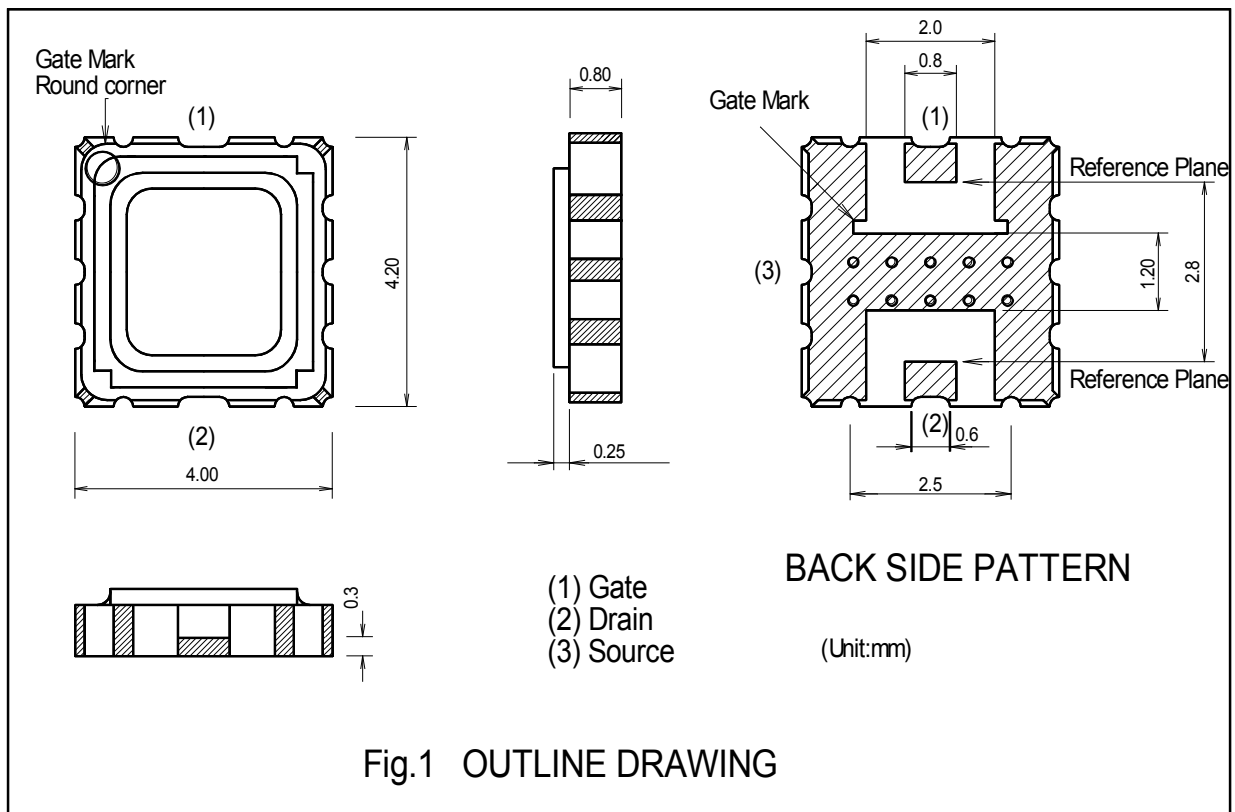
*1:Channel to case / Above parameters, ratings, limits are subject to change.

MGF0921A TYPICAL CHARACTERISTICS



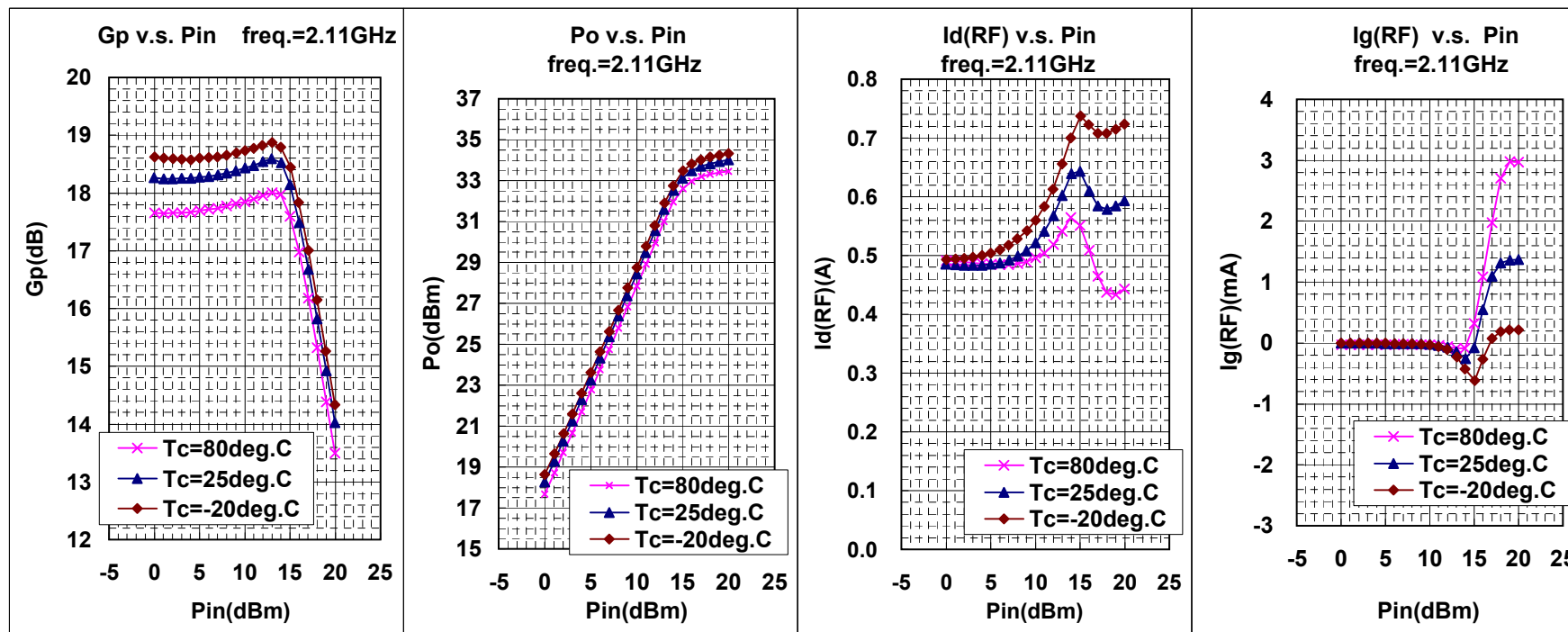
MGF0921A S PARAMETERS (Ta=25°C, VD=10V, ID=500mA, Reference Plane see Fig.1)

freq.	S11		S21		S12		S22		K	MAG/MSG
(MHz)	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)		(dB)
600	0.928	-120.29	6.597	111.05	0.018	31.80	0.605	-172.68	0.29	25.64
1000	0.922	-144.64	4.629	94.88	0.022	22.95	0.619	-173.49	0.37	23.23
1400	0.919	-156.53	3.312	82.95	0.023	17.64	0.633	-173.69	0.46	21.58
1800	0.918	-162.98	2.465	73.91	0.023	14.81	0.646	-173.51	0.59	20.30
2200	0.918	-167.59	1.943	66.76	0.022	13.62	0.657	-173.14	0.78	19.46
2600	0.918	-171.55	1.638	60.71	0.021	13.45	0.666	-172.72	0.97	18.92
3000	0.918	-174.74	1.467	55.23	0.020	13.81	0.673	-172.38	1.14	16.41
3400	0.917	-176.80	1.369	49.96	0.021	14.36	0.679	-172.19	1.13	15.92
3800	0.915	-178.13	1.306	44.67	0.022	14.88	0.684	-172.23	1.12	15.64
4200	0.912	-179.10	1.252	39.24	0.023	15.23	0.689	-172.51	1.13	15.19
4600	0.907	-178.57	1.195	33.65	0.025	15.31	0.692	-173.04	1.11	14.81
5000	0.901	-176.73	1.130	27.89	0.028	15.10	0.695	-173.79	1.07	14.40
5400	0.893	-173.69	1.060	22.01	0.030	14.57	0.698	-174.72	1.16	13.09
5800	0.884	-169.77	0.990	16.05	0.033	13.75	0.699	-175.77	1.23	11.91
6200	0.875	-165.38	0.927	10.04	0.036	12.62	0.699	-176.86	1.31	10.79
6600	0.865	-160.90	0.879	4.00	0.040	11.18	0.697	-177.90	1.35	9.89
7000	0.854	-156.64	0.851	-2.11	0.044	9.40	0.691	-178.80	1.39	9.13
7400	0.843	-152.74	0.848	-8.33	0.048	7.23	0.683	-179.47	1.40	8.72
7800	0.831	-149.18	0.871	-14.76	0.054	4.59	0.670	-179.82	1.31	8.71
8200	0.817	-145.73	0.917	-21.54	0.061	1.36	0.652	-179.47	1.22	8.93
8600	0.800	-142.03	0.981	-28.84	0.070	-2.57	0.630	-178.51	1.12	9.39
9000	0.778	-137.54	1.056	-36.86	0.082	-7.38	0.602	-177.26	1.03	10.07
9400	0.750	-131.70	1.132	-45.79	0.095	-13.23	0.571	-175.75	1.00	10.76
9800	0.711	-123.95	1.201	-55.85	0.112	-20.32	0.536	-173.84	1.01	9.78
10200	0.671	-113.89	1.253	-67.22	0.132	-28.83	0.502	-171.52	1.01	9.09
10600	0.636	-101.36	1.285	-80.02	0.154	-38.94	0.470	-169.20	1.01	8.57
11000	0.623	-86.68	1.295	-94.34	0.179	-50.78	0.447	-167.97	0.96	8.59
11400	0.643	-70.74	1.293	-110.12	0.205	-64.45	0.369	-169.96	0.95	8.00
11800	0.699	-55.29	1.297	-127.21	0.231	-79.99	0.293	-178.54	0.90	7.49
12200	0.778	-43.12	1.342	-145.25	0.256	-97.34	0.281	-154.64	0.84	7.20



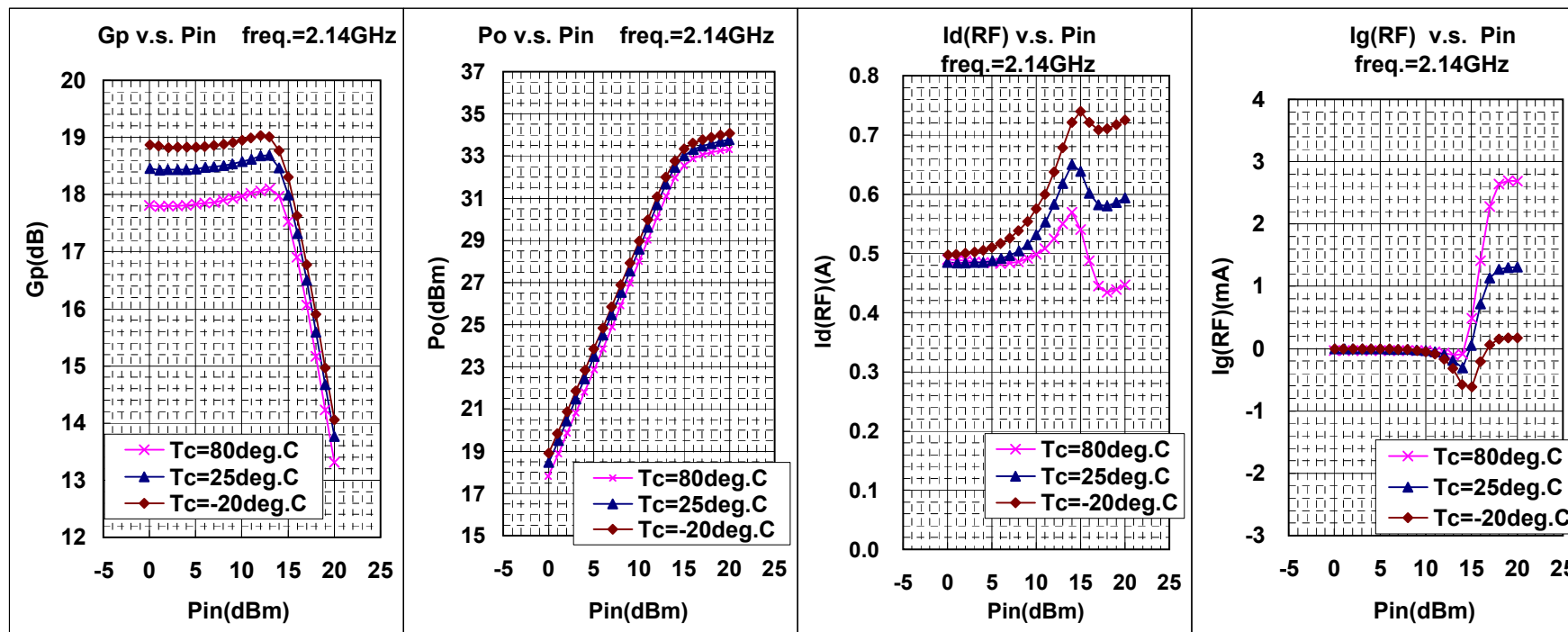
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Gp,Po,Id(RF),Ig(RF) v.s. Pin

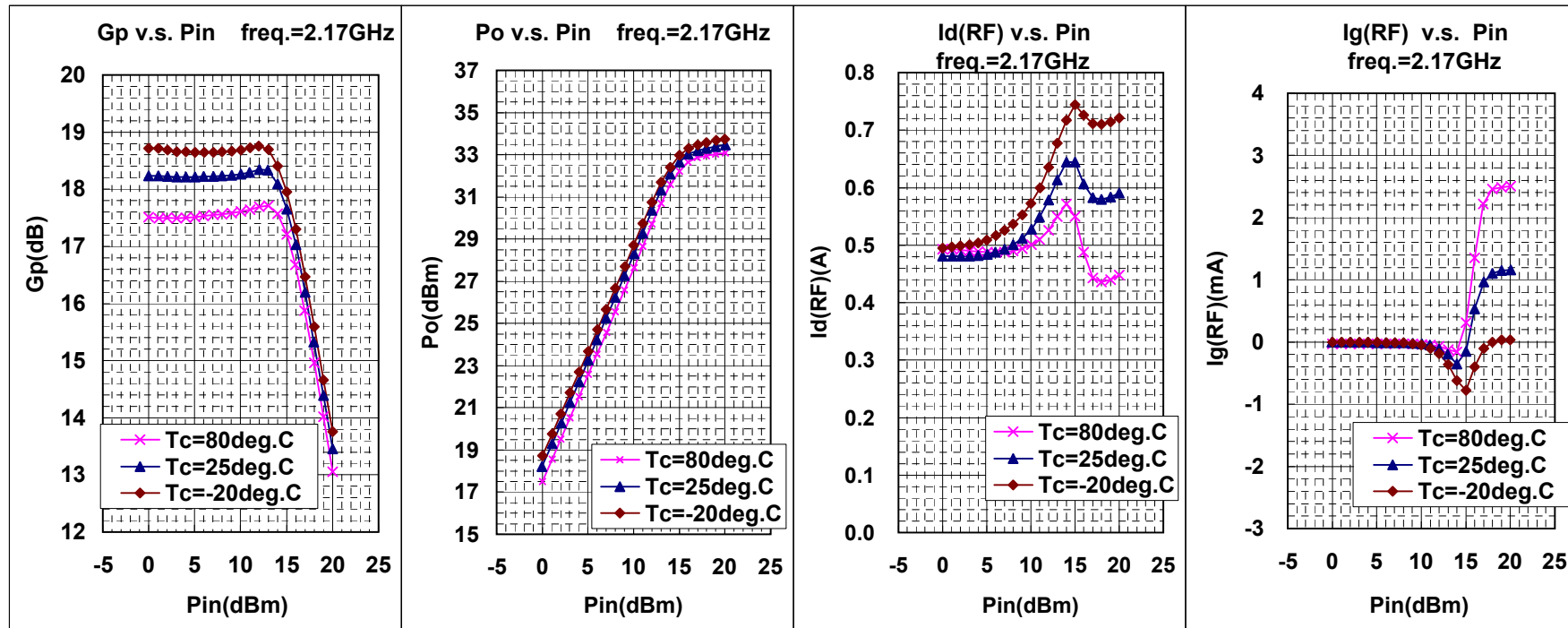


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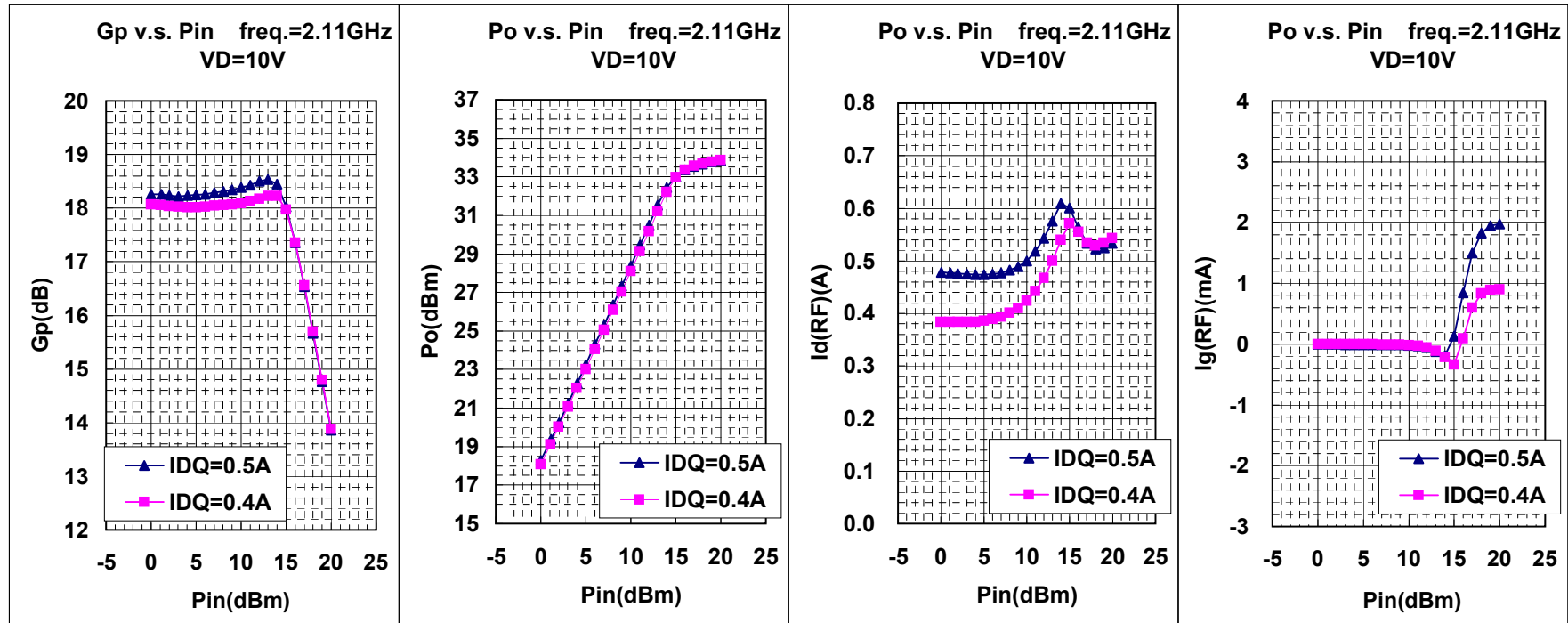
Gp, Po, Id(RF), Ig(RF) v.s. Pin



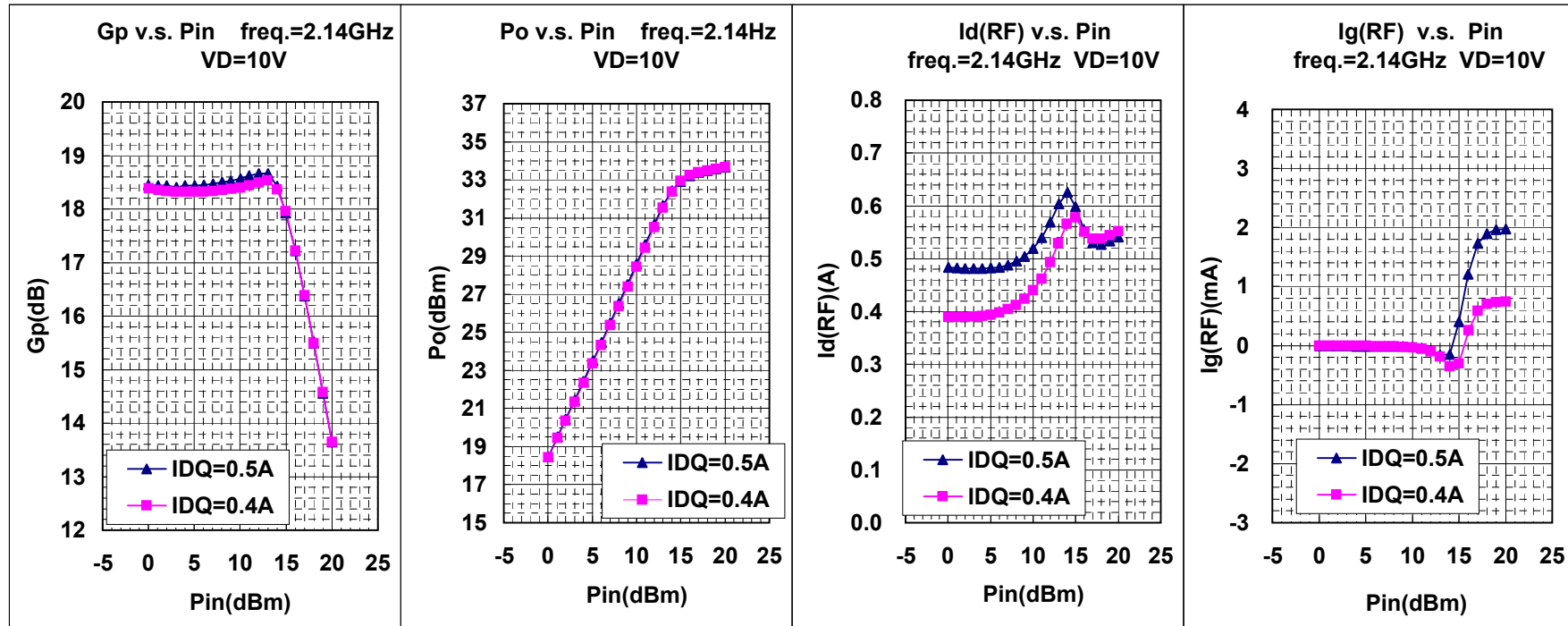
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Gp, Po, Id(RF), Ig(RF) v.s. Pin



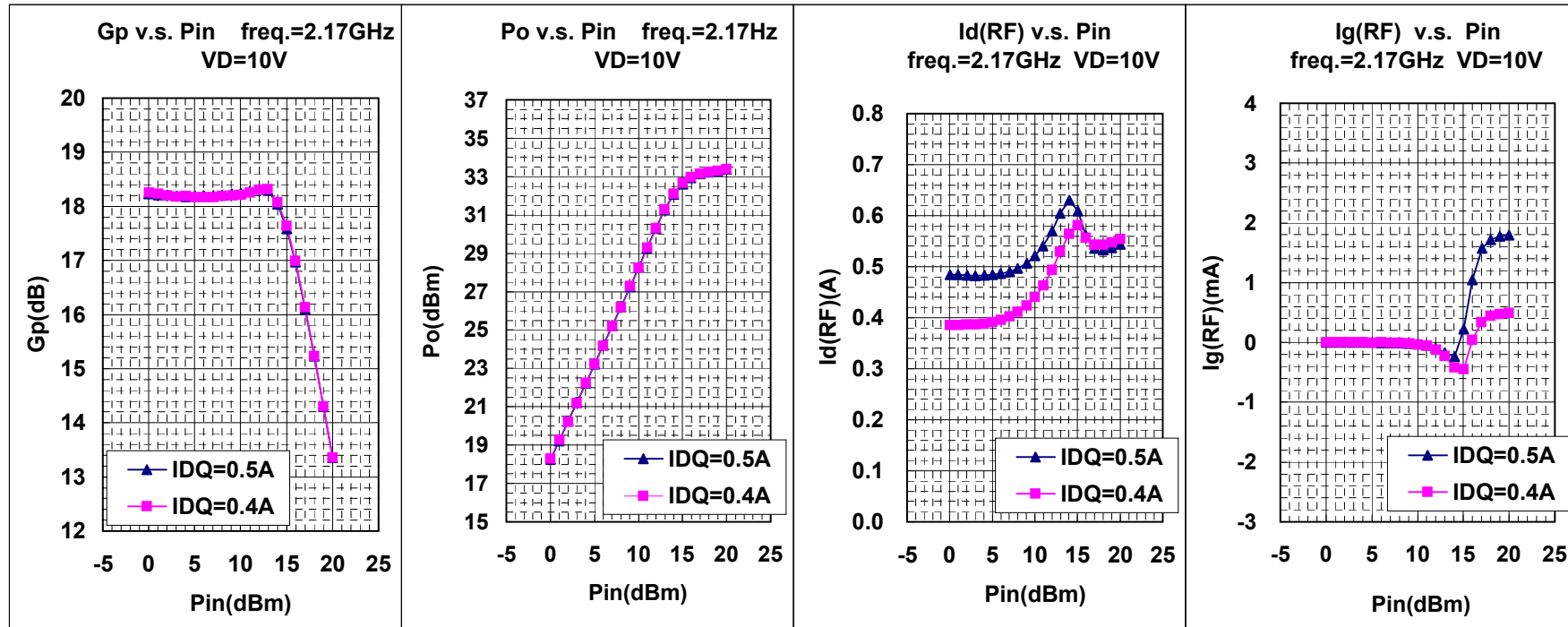
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Gp,Po,Id(RF),Ig(RF) v.s. Pin



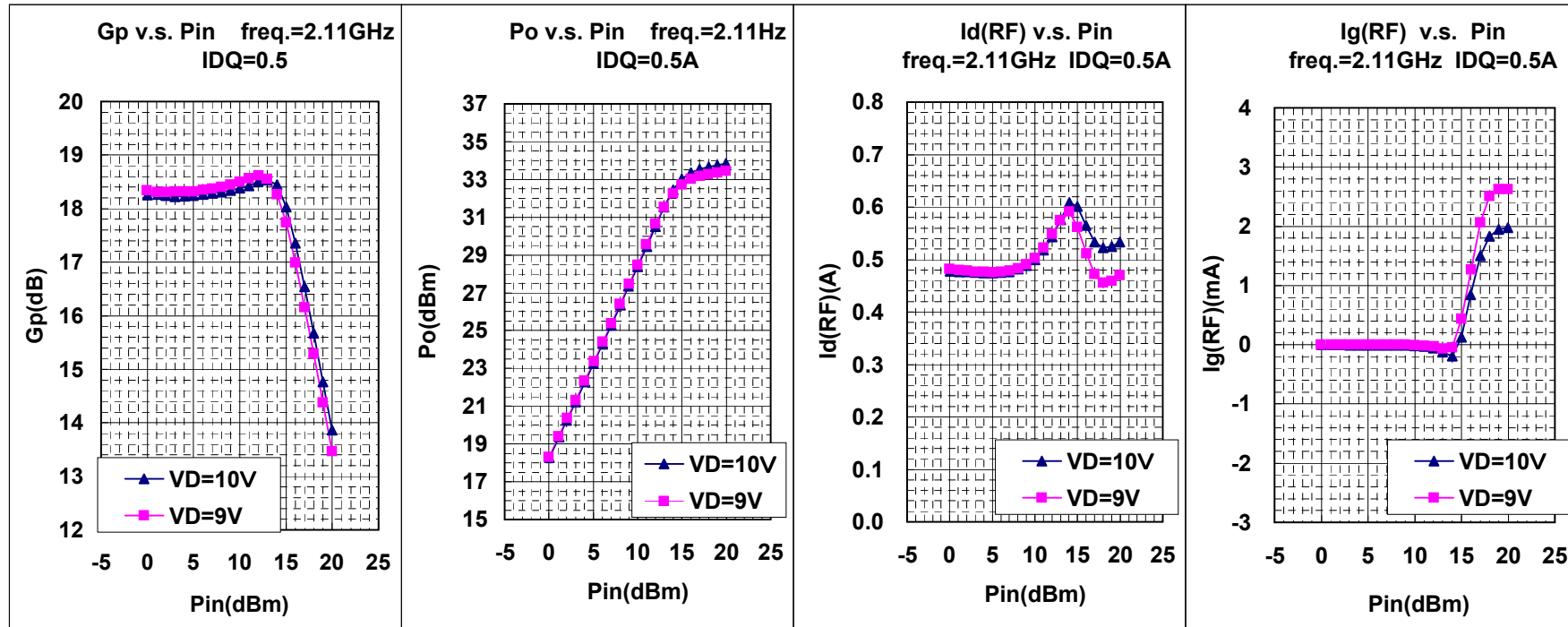
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Gp,Po,Id(RF),Ig(RF) v.s. Pin



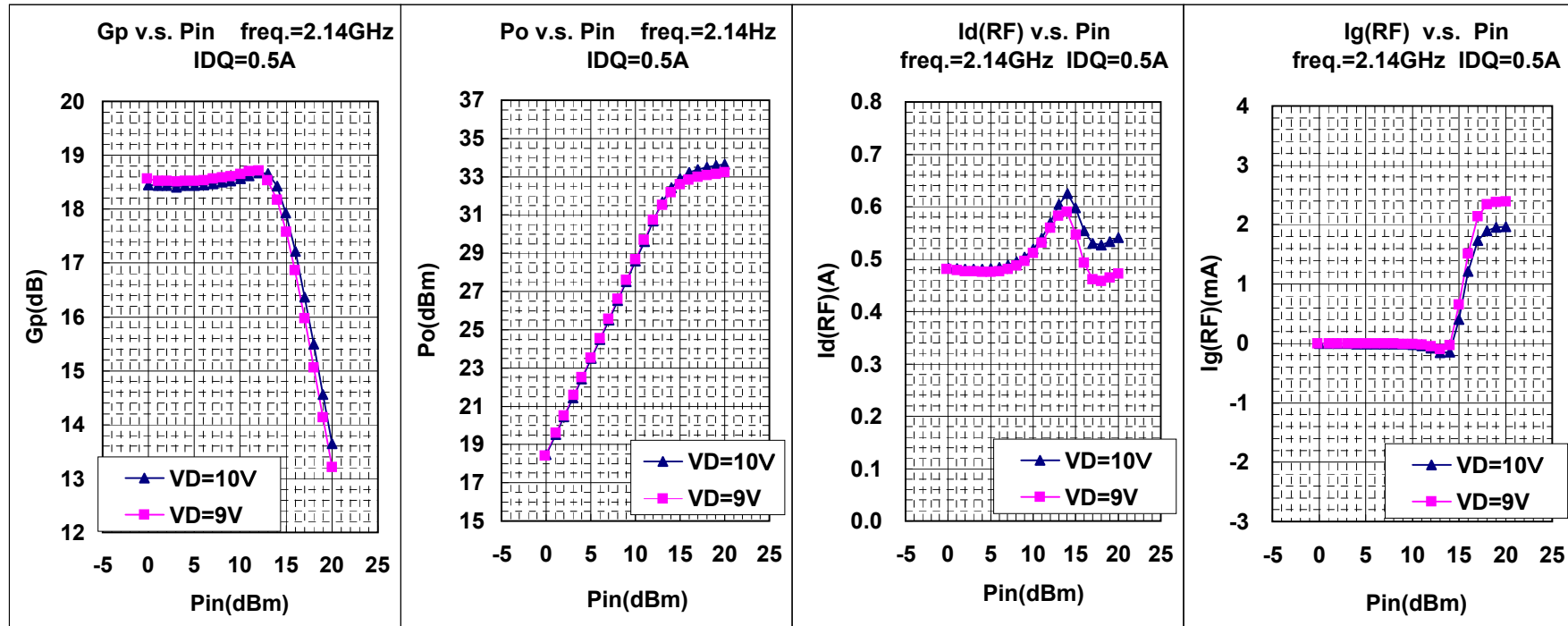
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Gp,Po,Id(RF),Ig(RF) v.s. Pin



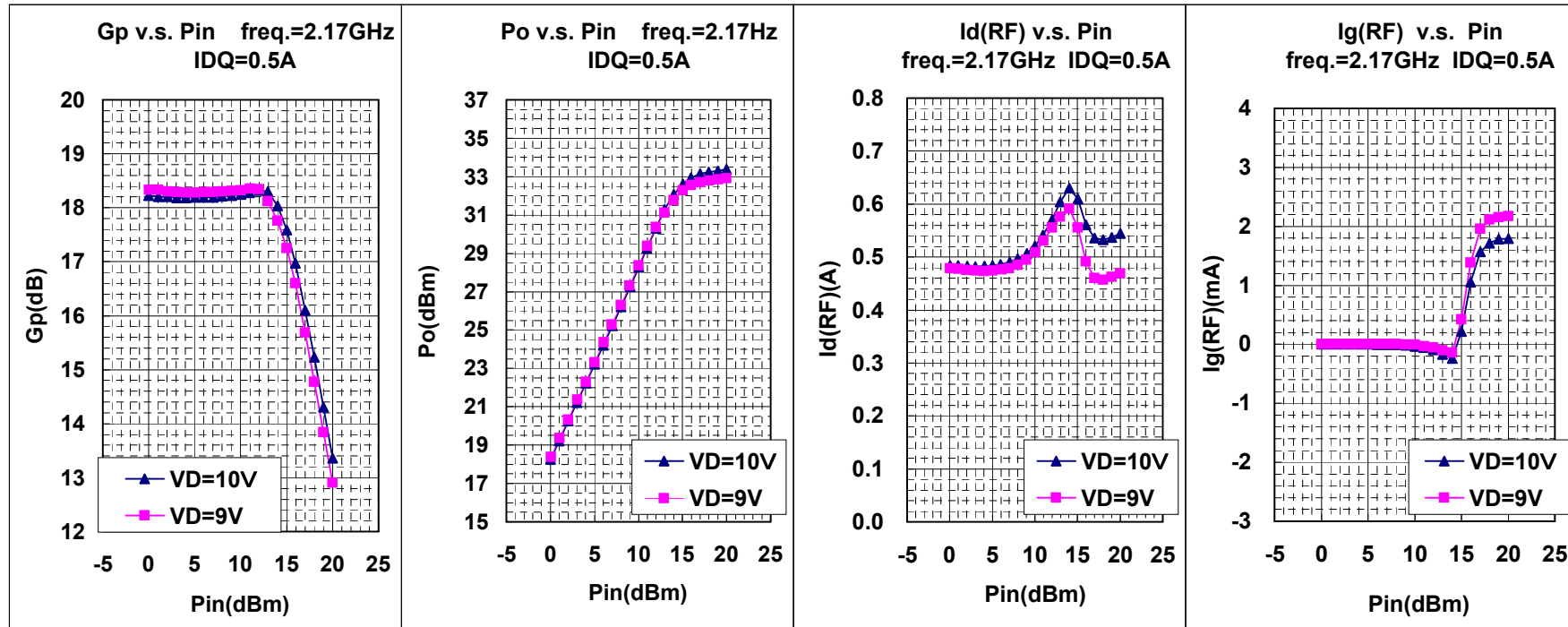
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Gp,Po,Id(RF),Ig(RF) v.s. Pin



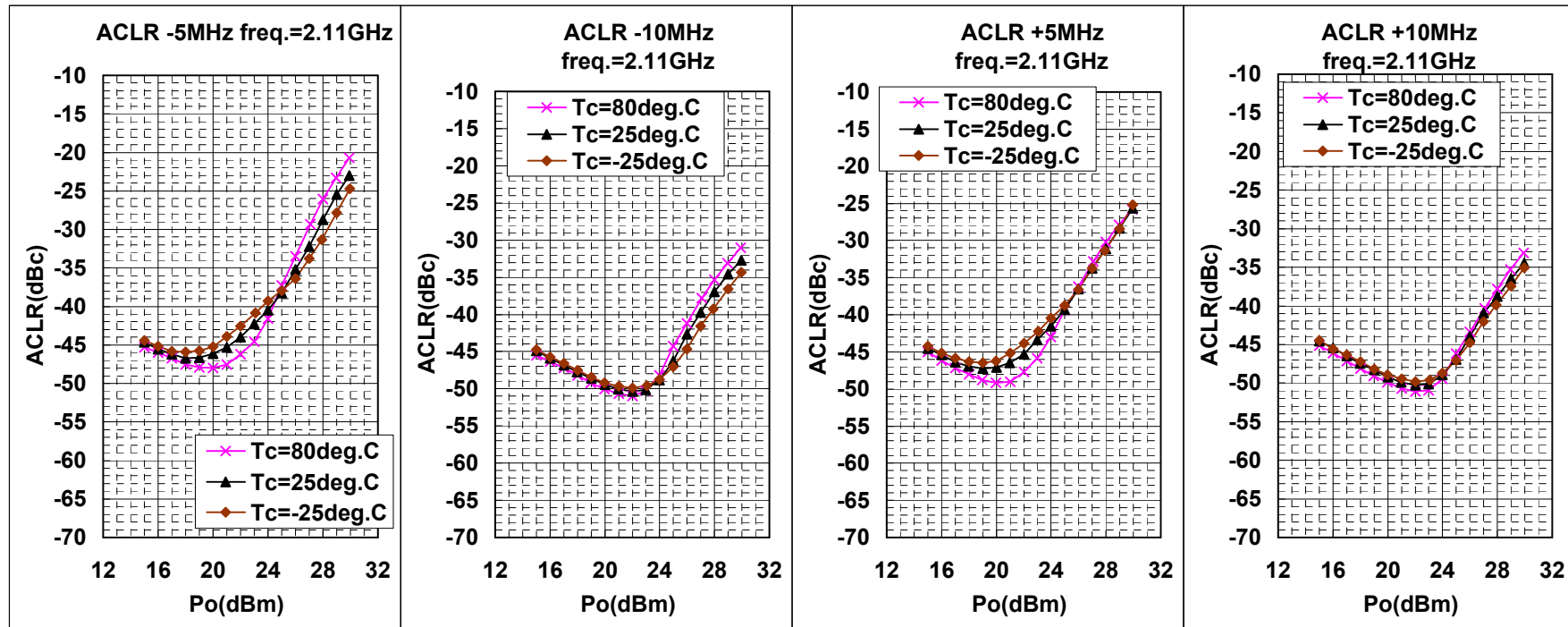
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Gp,Po,Id(RF),Ig(RF) v.s. Pin



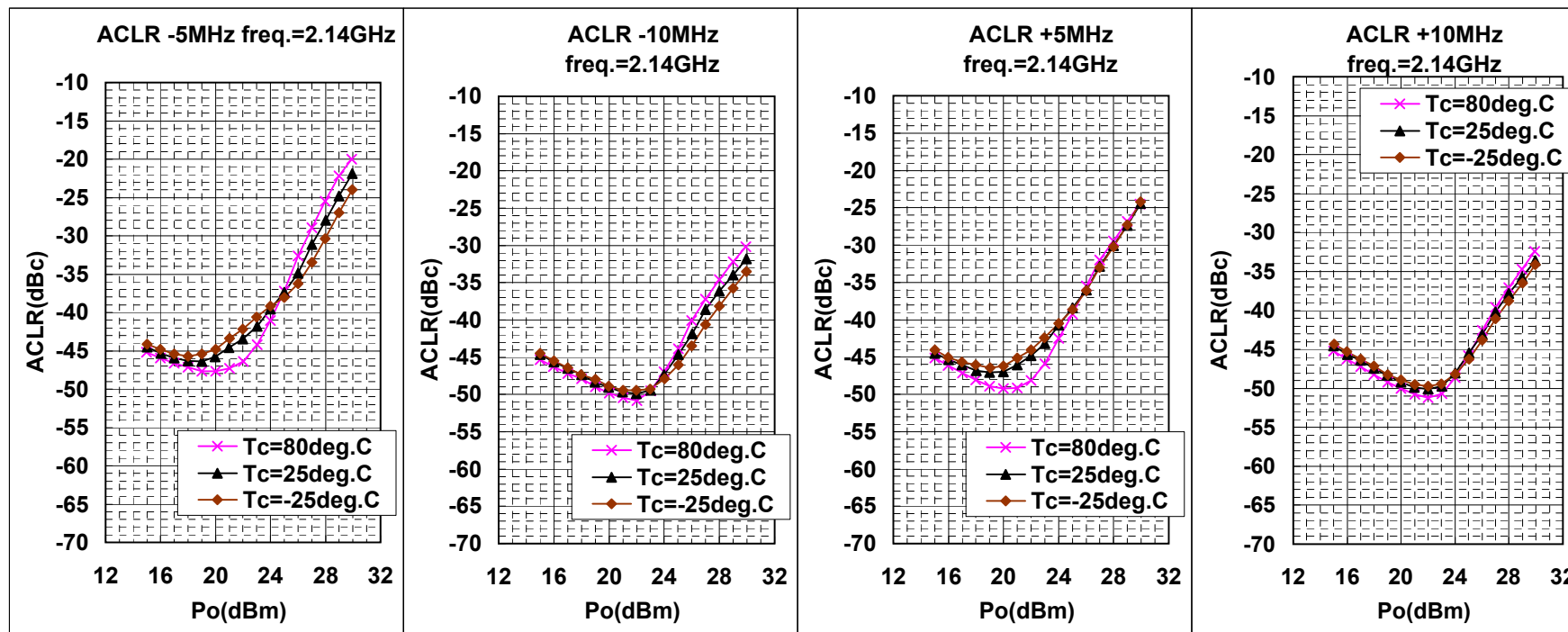
MGF0921A RF TEST DATA(CW)
Gp,Po,Id(RF),Ig(RF) v.s. Pin



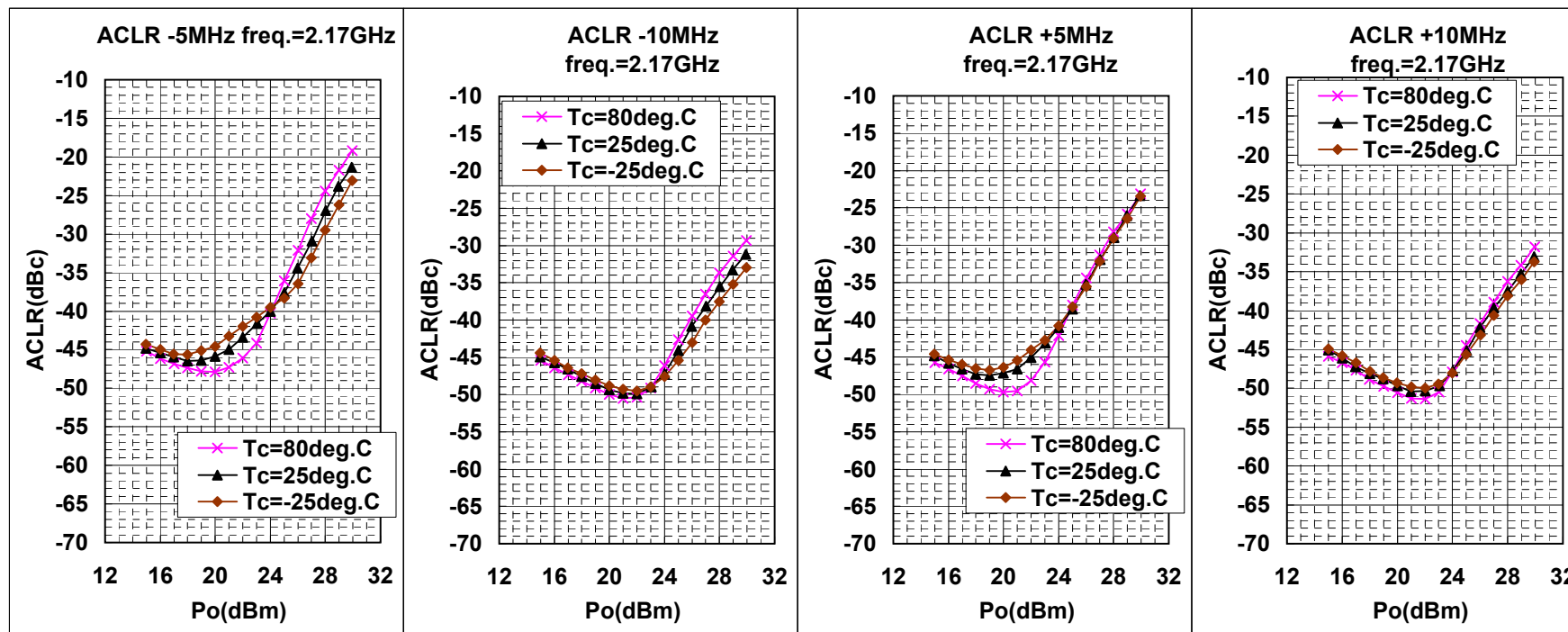
MGF0921A RF TEST DATA(W-CDMA) VD=10V,IDQ=0.5A
ACLR v.s. Po 3GPP TEST MODEL1 64ch's 2carrier Signal



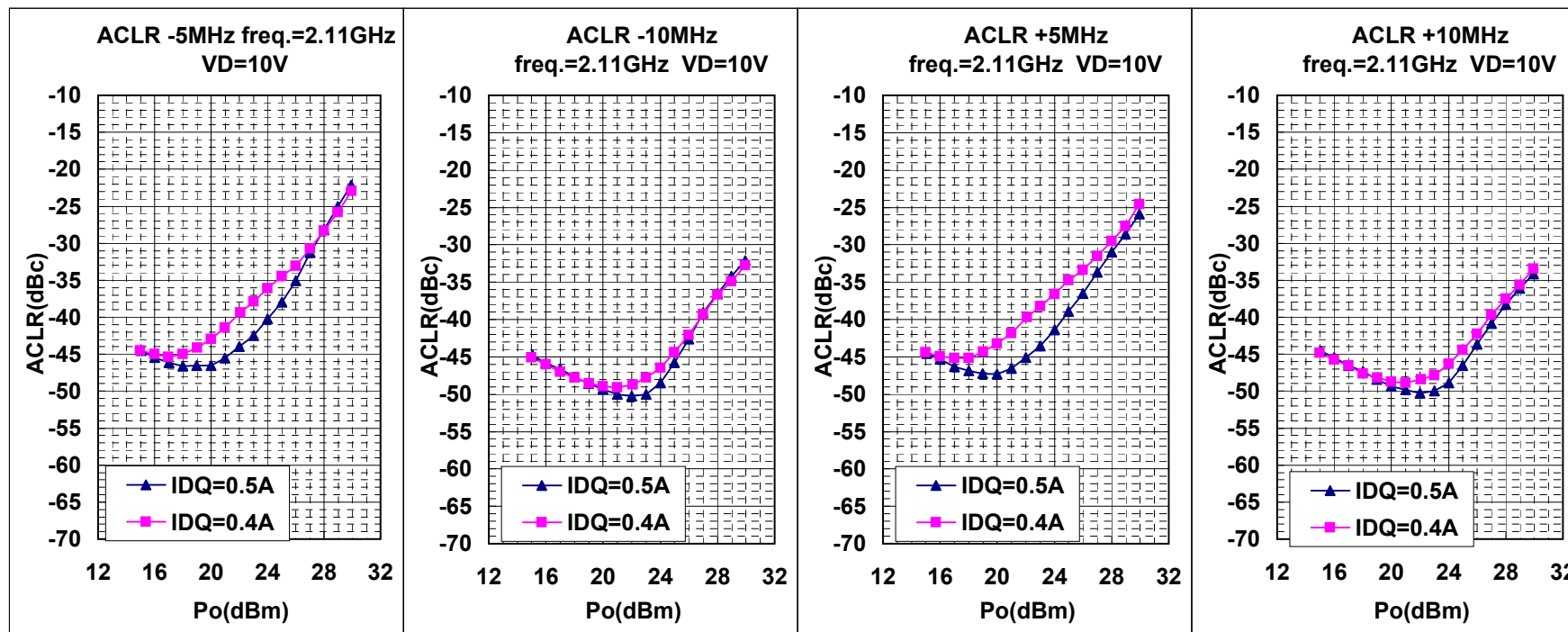
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 ACLR v.s. Po 3GPP TEST MODEL1 64ch's 2carrier Signal



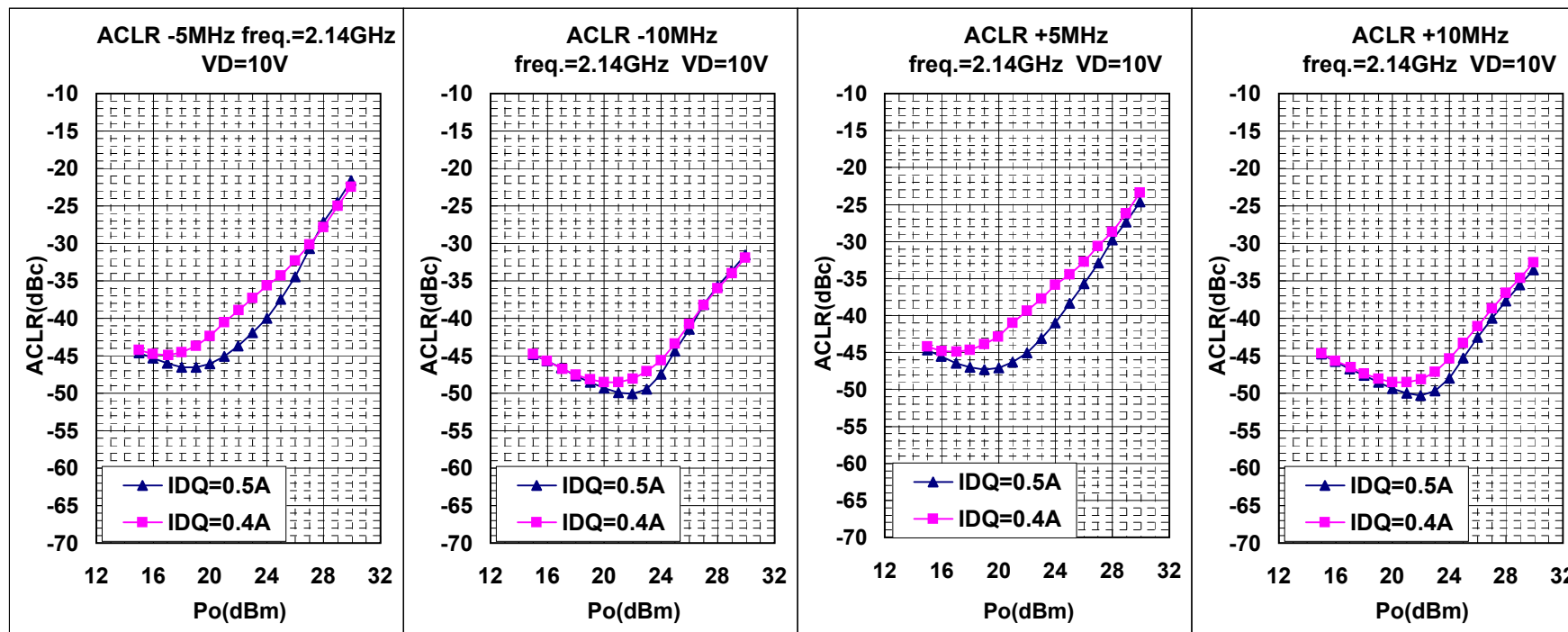
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 ACLR v.s. Po 3GPP TEST MODEL1 64ch's 2carrier Signal



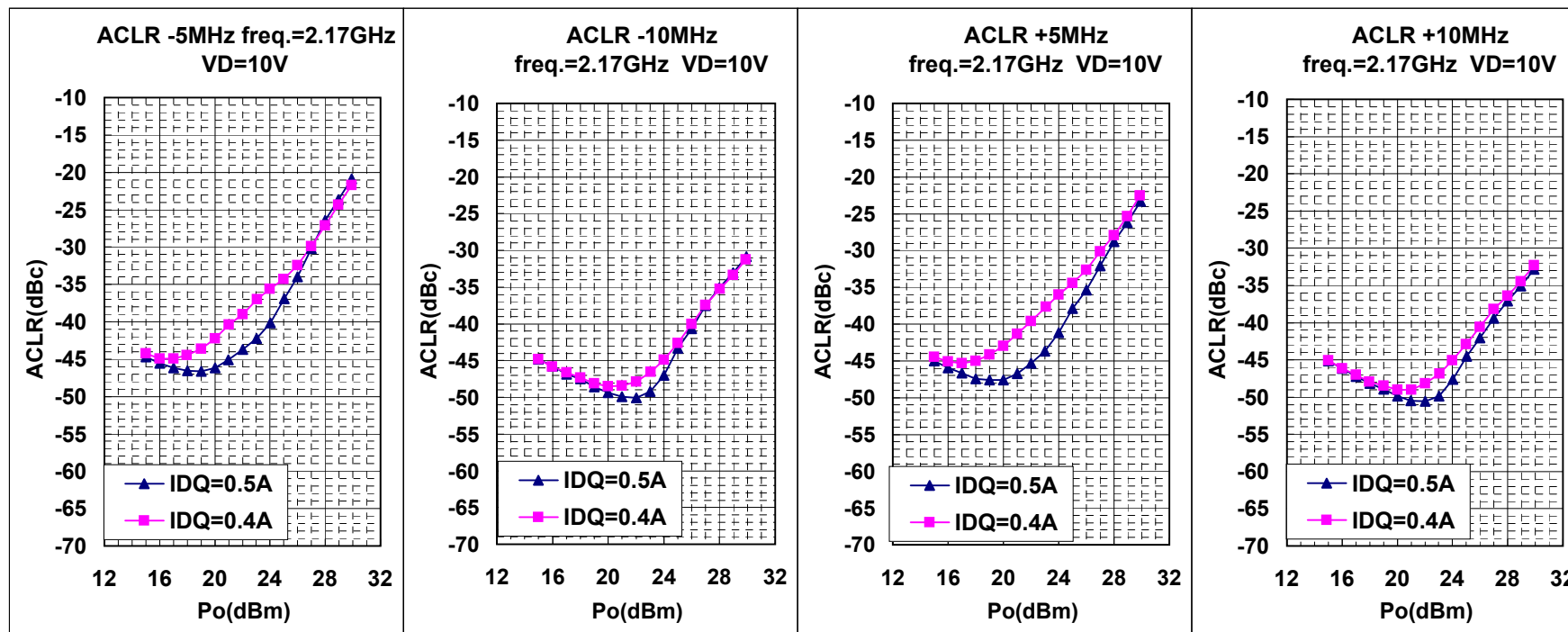
MGF0921A RF TEST DATA(W-CDMA)
ACLR v.s. Po 3GPP TEST MODEL1 64ch's 2carrier Signal



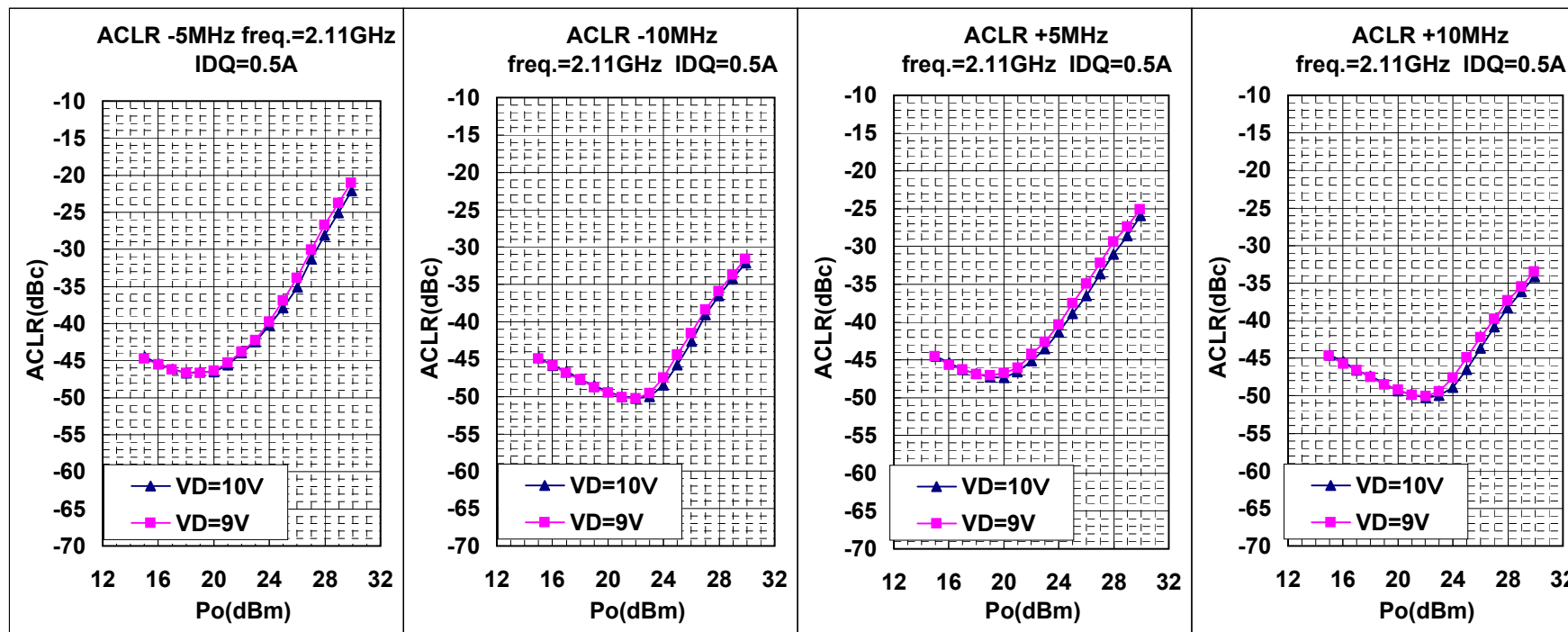
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ACLR v.s. Po 3GPP TEST MODEL1 64ch's 2carrier Signal



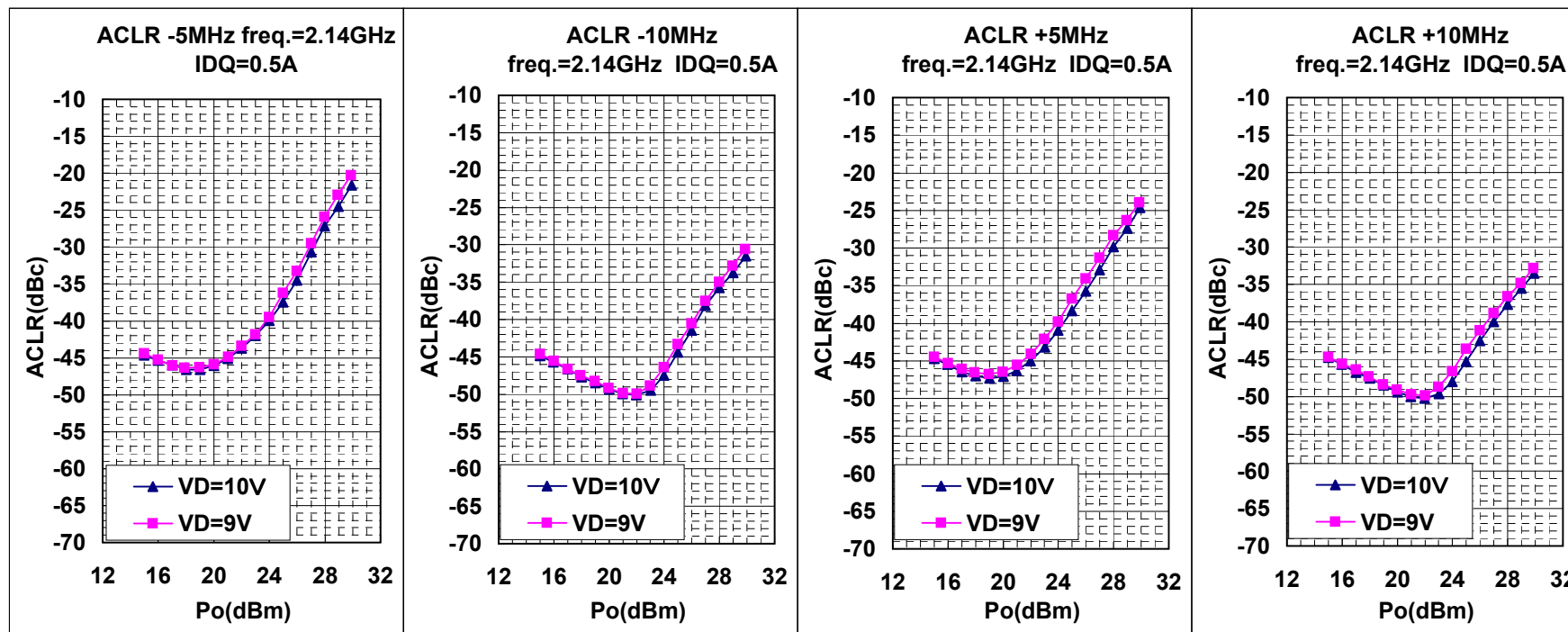
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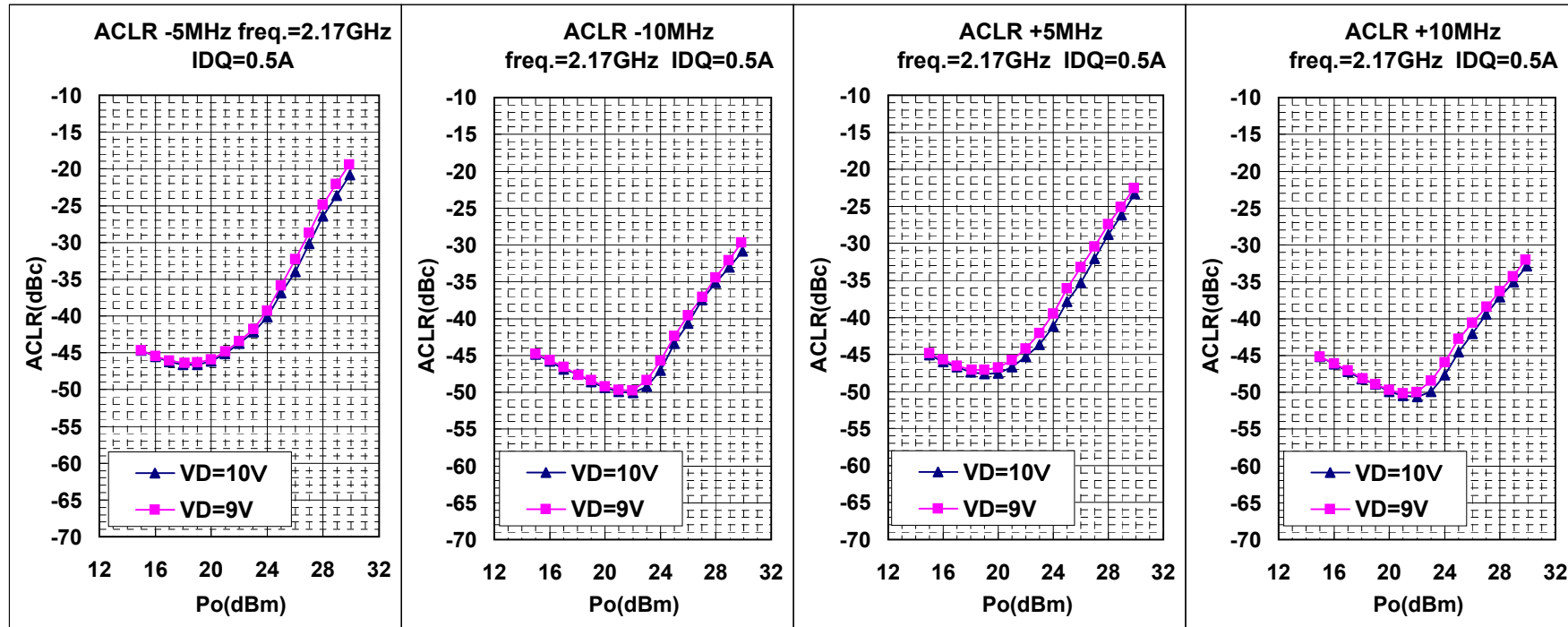
MGF0921A RF TEST DATA(W-CDMA)
ACLR v.s. Po 3GPP TEST MODEL1 64ch's 2carrier Signal



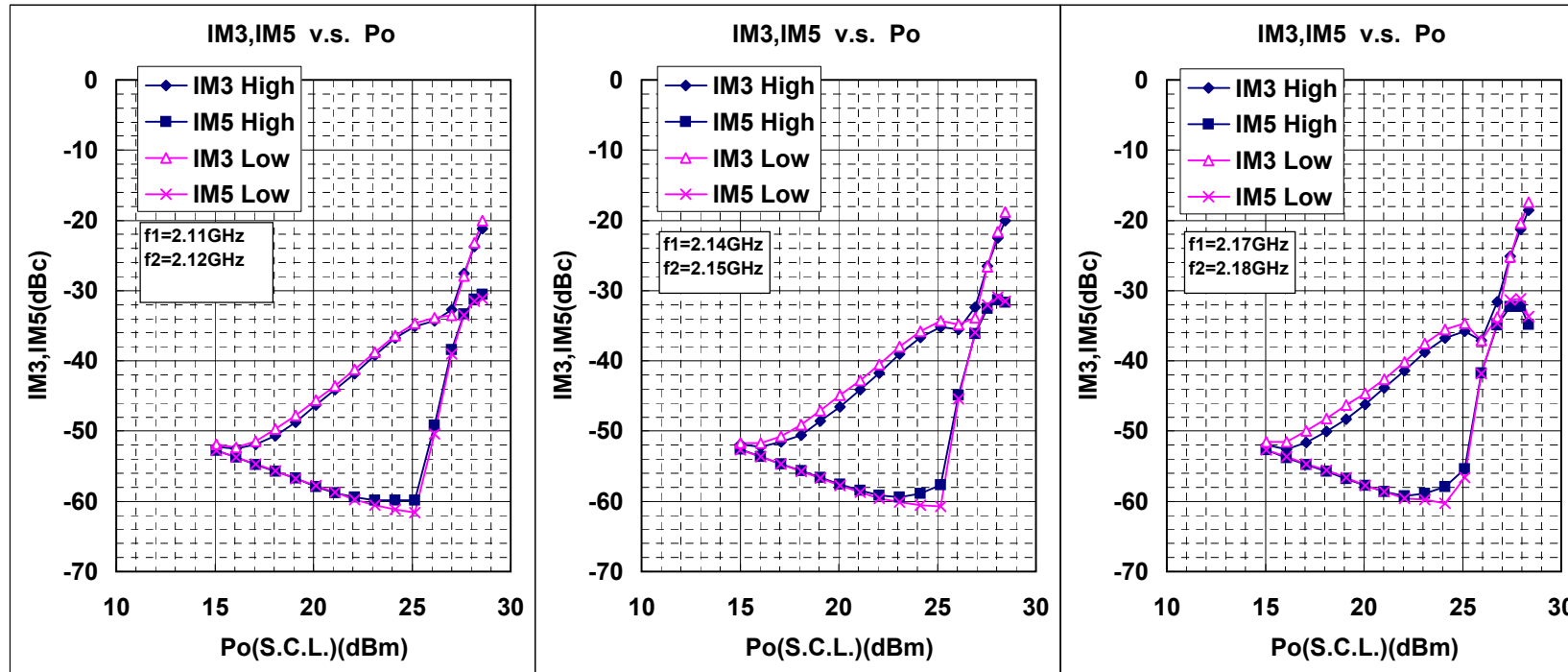
MGF0921A RF TEST DATA(W-CDMA)
ACLR v.s. Po 3GPP TEST MODEL1 64ch's 2carrier Signal



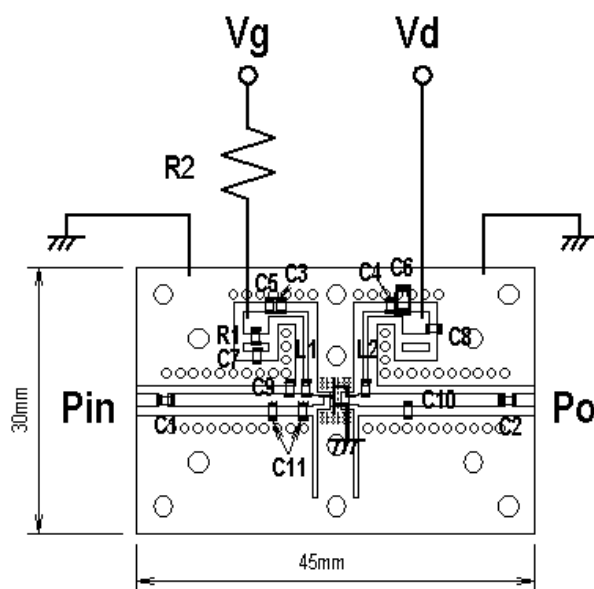
MGF0921A RF TEST DATA(W-CDMA)
ACLR v.s. Po 3GPP TEST MODEL1 64ch's 2carrier Signal



MGF0921A RF TEST DATA $V_D=10V, I_{DQ}=0.5A$
IM3,IM5 v.s. P_{in}



MGF0921A TEST FIXTURE $f=2.11\text{-}2.17\text{GHz}$



$C1, C2, C3, C4 = 20\text{pF}$
 $C5, C7, C8 = 1000\text{pF}$
 $C9, C10, C11 = 2\text{pF}$
 $C6 = 4.7\mu\text{F}$
 $L1, L2 = 12\text{nH}$
 $R1 = 51\text{ohm}$
 $R2 = 200\text{ohm}$

Board material: FR4 Thickness=0.8(mm)
 Specific dielectric constant=4.4

L & S BAND GaAs FET [SMD non – matched]**Requests Regarding Safety Designs**

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